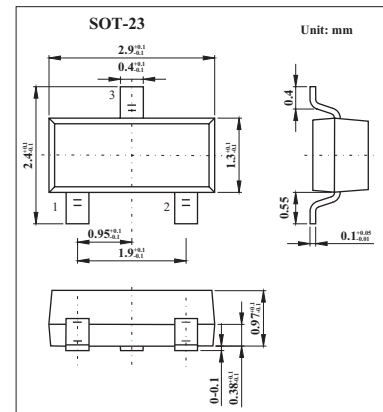


## Schottky Barrier Diode

## 1SS366

## ■ Features

- Series connection of 2 elements in a very small-sized package facilitates high-density mounting and permits 1SS366-applied equipment to be made smaller.
- Small interterminal capacitance.
- Low forward voltage.
- High breakdown voltage.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	10	V
Forward Current	$I_F$	35	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_{F(1)}$	$I_F = 1\text{ mA}$	350		420	mV
	$V_{F(2)}$	$I_F = 10\text{ mA}$	480		580	mV
Forward Current	$I_F$	$V_F = 1\text{ V}$	35			mA
Reverse Current	$I_{R(1)}$	$V_R = 2\text{ V}$			0.2	$\mu\text{ A}$
	$I_{R(2)}$	$V_R = 10\text{ V}$			10	$\mu\text{ A}$
Interterminal Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.85	pF
Forward Voltage Difference	$\Delta V_F$	$I_F = 10\text{ mA}$			10	mV
Interterminal Capacitance Difference	$\Delta C$	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.1	pF

## ■ Marking

Marking	FH